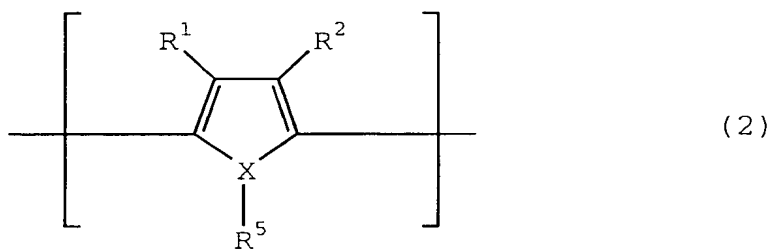
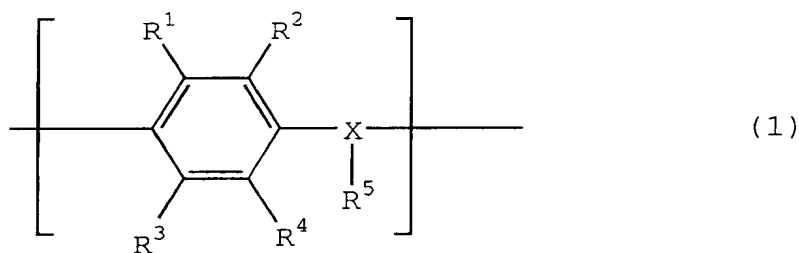


WHAT IS CLAIMED IS:

1. A niobium powder for capacitors, containing niobium monoxide crystal and hexaniobium monoxide crystal.
2. The niobium powder for capacitors as claimed in claim 1, wherein the content of the niobium monoxide crystal is from 0.05 to 20 % by mass.
3. The niobium powder for capacitors as claimed in claim 1, wherein the content of the hexaniobium monoxide crystal is from 0.05 to 20 % by mass.
4. The niobium powder for capacitors as claimed in claim 1, which contains a partially nitrated niobium powder.
5. The niobium powder for capacitors as claimed in claim 4, wherein the nitrated amount is 10 ~ 100,000 ppm by mass.
6. A sintered body using the niobium powder for capacitors claimed in claim 1.
7. A capacitor fabricated from the sintered body claimed in claim 6 as one part electrode, a dielectric material formed on the surface of the sintered body, and another part electrode provided on the dielectric material.
8. The capacitor as claimed in claim 7, wherein the dielectric material is mainly composed of niobium oxide.
9. The capacitor as claimed in claim 8, wherein the niobium oxide is formed by electrolytic oxidation.

10. The capacitor as claimed in claim 7, wherein the another part electrode is at least one material selected from an electrolytic solution, an organic semiconductor or an inorganic semiconductor.

11. The capacitor as claimed in claim 10, wherein the another part electrode is composed of an organic semiconductor and the organic semiconductor is at least one organic semiconductor selected from the group consisting of an organic semiconductor comprising a benzopyrroline tetramer and chloranile, an organic semiconductor mainly comprising tetrathiotetracene, an organic semiconductor mainly comprising tetracyanoquinodimethane and an organic semiconductor mainly comprising an electrically conducting polymer obtained by doping a dopant into a polymer comprising two or more repeating units represented by the following formula (1) or (2):



(wherein R¹ to R⁴, which may be the same or different, each represents a hydrogen atom, an alkyl group having from 1 to 6 carbon atoms or an alkoxy group having from 1 to 6 carbon atoms, X represents an oxygen atom, a sulfur atom or a nitrogen atom, R⁵ is present only when X is a nitrogen atom and represents a hydrogen atom or an

alkyl group having from 1 to 6 carbon atoms, and each of the pairs R¹ and R², and R³ and R⁴ may combine with each other to form a ring).

12. The capacitor as claimed in claim 11, wherein the organic semiconductor is at least one member selected from polypyrrole, polythiophene or substitution derivatives thereof.

13. The niobium powder for capacitors as claimed in claim 2, which contains a partially nitrated niobium powder.

14. The niobium powder for capacitors as claimed in claim 3, which contains a partially nitrated niobium powder.

15. A niobium powder for capacitors, containing niobium monoxide crystal or hexaniobium monoxide crystal.

16. The niobium powder for capacitors as claimed in claim 15, of which an oxidized amount is from 10,000 to 200,000 ppm by mass.

17. The niobium powder for capacitors as claimed in claim 15, which has an average particle size of 0.1 μm to tens of μm .

18. The niobium powder for capacitors as claimed in claim 15, which contains a partially nitrated niobium powder.

19. The niobium powder for capacitors as claimed in claim 16, which contains a partially nitrated niobium powder.

20. The niobium powder for capacitors as claimed in claim 17, which contains a partially nitrated niobium powder.

21. The niobium powder for capacitors as claimed in claim 18, wherein the nitrated amount is 10 ~ 100,000 ppm by mass.

22. The niobium powder for capacitors as claimed in claim 19, wherein the nitrided amount is 10 ~ 100,000 ppm by mass.

23. The niobium powder for capacitors as claimed in claim 20, wherein the nitrided amount is 10 ~ 100,000 ppm by mass.

24. A sintered body using the niobium powder for capacitors claimed in claim 15.

25. A capacitor fabricated from the sintered body claimed in claim 24 as one part electrode, a dielectric material formed on the surface of the sintered body, and another part electrode provided on the dielectric material.

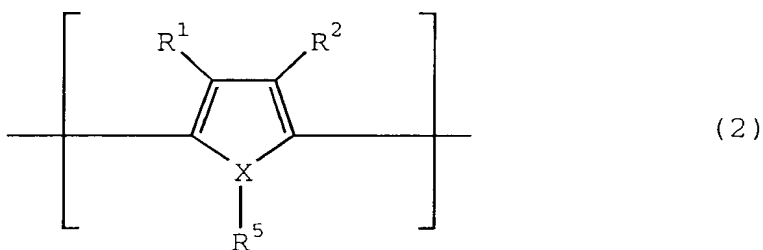
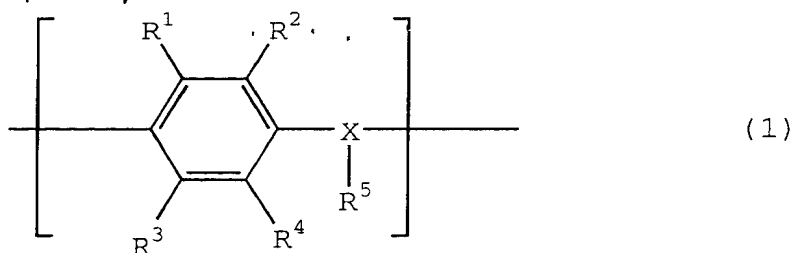
26. The capacitor as claimed in claim 25 wherein the dielectric material is mainly composed of niobium oxide.

27. The capacitor as claimed in claim 26, wherein the niobium oxide is formed by electrolytic oxidation.

28. The capacitor as claimed in claim 25, wherein the another part electrode is at least one material selected from an electrolytic solution, an organic semiconductor and an inorganic semiconductor.

29. The capacitor as claimed in claim 28, wherein the another part electrode is composed of an organic semiconductor and the organic semiconductor is at least one organic semiconductor selected from the group consisting of an organic semiconductor comprising a benzopyrroline tetramer and chloranile, an organic semiconductor mainly comprising tetrathiotetracene, an organic semiconductor mainly comprising tetracyanoquinodimethane and an organic semiconductor mainly comprising an electrically conducting polymer obtained by doping a dopant into a

polymer comprising two or more repeating units represented by the following formula (1) or (2):



wherein R^1 to R^4 , which may be the same or different, each represents a hydrogen atom, an alkyl group having from 1 to 6 carbon atoms or an alkoxy group having from 1 to 6 carbon atoms, X represents an oxygen atom, a sulfur atom or a nitrogen atom, R^5 is present only when X is a nitrogen atom and represents a hydrogen atom or an alkyl group having from 1 to 6 carbon atoms, and each of the pairs R^1 and R^2 , and R^3 and R^4 may combine with each other to form a ring.

30. The capacitor as claimed in claim 29, wherein the polymer comprising two or more repeating units represented by the formula (1) or (2) is at least one member selected from polypyrrole, polythiophene and substitution derivatives thereof.